

PUMD6

50 V, 100 mA NPN/PNP Resistor-Equipped Transistor; R1 = 4.7 k Ω , R2 = open

27 April 2023

Product data sheet

1. General description

NPN/PNP Resistor-Equipped Transistor (RET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: PUMH7 PNP/PNP complement: PUMB3

2. Features and benefits

- Built-in bias resistors
- · Simplifies circuit design
- Reduces component count
- · Reduces pick and place costs
- AEC-Q101 qualified

3. Applications

- Digital application in industrial segments
- · Switching loads
- · Low current peripheral driver
- · Controlling IC inputs
- Cost-saving alternative to BC847 / BC857 series in digital applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor						•	
V _{CEO}	collector-emitter voltage	open base	[1]	-	-	50	V
Io	output current		[1]	-	-	100	mA
R1	bias resistor 1 (input)	T _{amb} = 25 °C	[2]	3.3	4.7	6.1	kΩ

- [1] For the PNP transistor with negative polarity.
- [2] See section "Test information" for resistor calculation and test conditions.



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	I1	input (base) TR1	□6 □5 □4	
3	O2	output (collector) TR2		
4	GND2	GND (emitter) TR2		TR1
5	12	input (base) TR2	H ₁ H ₂ H ₃	R1 R1
6	O1	output (collector) TR1	TSSOP6 (SOT363)	GND1 I1 O2 006aaa269

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PUMD6		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	SOT363		

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PUMD6	D%6

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transiste	or		,			
V _{CBO}	collector-base voltage	open emitter	[1]	-	50	V
V _{CEO}	collector-emitter voltage	open base	[1]	-	50	V
V _{EBO}	emitter-base voltage	open collector	[1]	-	5	V
V _I	input voltage	TR1 (NPN)		-5	30	V
		TR2 (PNP)		-30	5	V
Io	output current		[1]	-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	200	mW
Per device	'		,			
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	300	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] For the PNP transistor with negative polarity.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.

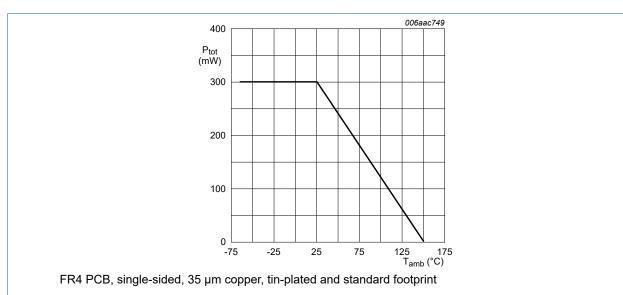


Fig. 1. Per device: Power derating curve

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	625	K/W
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	416	K/W

[1] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint.

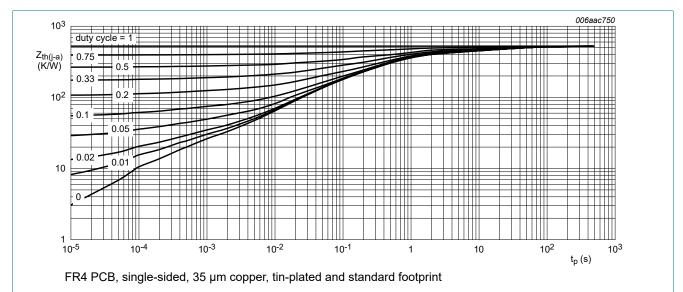


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	tor						
V _{(BR)CBO}	collector-base breakdown voltage	$I_C = 100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	[1]	50	-	-	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	$I_C = 2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	50	-	-	V
I _{CBO}	collector-base cut-off current	V _{CB} = 50 V; I _E = 0 A; T _{amb} = 25 °C	[1]	-	-	100	nA
I _{CEO}	collector-emitter cut-off	V _{CE} = 30 V; I _B = 0 A; T _{amb} = 25 °C	[1]	-	-	100	nA
	current	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}; T_{j} = 150 ^{\circ}\text{C}$	[1]	-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	[1]	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 1 mA; T _{amb} = 25 °C	[1]	200	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 5 \text{ mA}; I_B = 0.25 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	-	-	100	mV
$V_{I(off)}$	off-state input voltage	V _{CE} = 5 V; I _C = 100 μA; T _{amb} = 25 °C	[1]	-	585	500	mV
V _{I(on)}	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 10 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	1.3	0.88	-	V
R1	bias resistor 1 (input)	T _{amb} = 25 °C	[2]	3.3	4.7	6.1	kΩ
TR1 (NPN)	·						·
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 \text{ °C}$		-	-	2.5	pF
f _T	transition frequency	V_{CE} = 5 V; I_{C} = 10 mA; f = 100 MHz; T_{amb} = 25 °C	[3]	-	230	-	MHz
TR2 (PNP)	'						
C _c	collector capacitance	V_{CB} = -10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	-	3	pF
f _T	transition frequency	V_{CE} = -5 V; I_{C} = -10 mA; f = 100 MHz; T_{amb} = 25 °C	[3]	-	180	-	MHz

For the PNP transistor with negative polarity. See section "Test information" for resistor calculation and test conditions. [2] [3]

Characteristics of built-in transistor

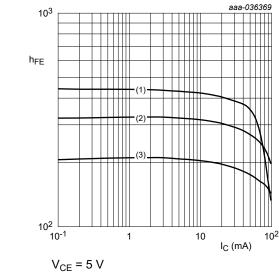


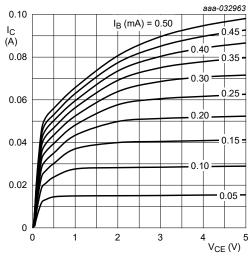
Fig. 3.

 $(1) T_{amb} = 100 °C$

(2) $T_{amb} = 25 \, ^{\circ}C$

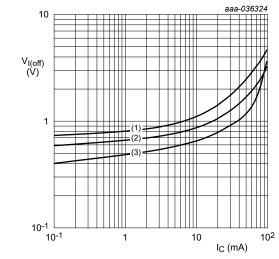
(3) $T_{amb} = -40 \, ^{\circ}C$ TR1 (NPN): DC current gain as a function of

collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$

Fig. 4. TR1 (NPN): Collector current as a function of collector-emitter voltage; typical values



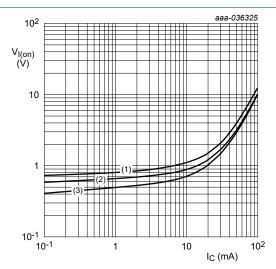
 $V_{CE} = 5 V$

(1) $T_{amb} = -40 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

TR1 (NPN): Off-state input voltage as a function | Fig. 6. Fig. 5. of collector current; typical values

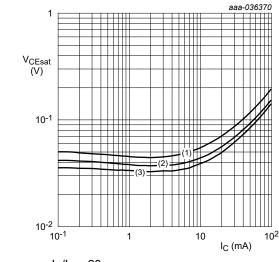


 $V_{CE} = 0.3 V$

(1) T_{amb} = - 40 °C (2) T_{amb} = 25 °C

(3) $T_{amb} = 100 \, ^{\circ}C$

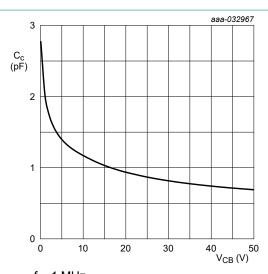
TR1 (NPN): On-state input voltage as a function of collector current; typical values



 $I_C/I_B = 20$ (1) $T_{amb} = 100 \, ^{\circ}C$

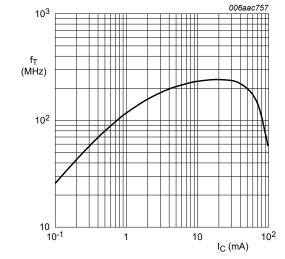
(2) $T_{amb} = 25 \,^{\circ}\text{C}$ (3) $T_{amb} = -40 \,^{\circ}\text{C}$

Fig. 7. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



f = 1 MHz $T_{amb} = 25 \, ^{\circ}C$

Fig. 8. TR1 (NPN): Collector capacitance as a function of collector-base voltage; typical values

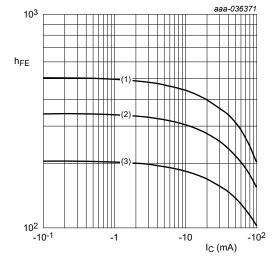


f = 100 MHz

T_{amb} = 25 °C

 $V_{CE} = 5 V$

TR1 (NPN): Transition frequency as a function Fig. 9. of collector current; typical values of built-in transistor



 $V_{CE} = -5 V$

(1) T_{amb} = 100 °C (2) T_{amb} = 25 °C

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig. 10. TR2 (PNP): DC current gain as a function of collector current; typical values

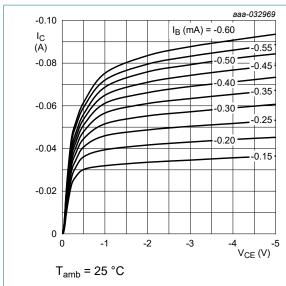
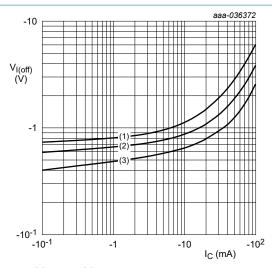


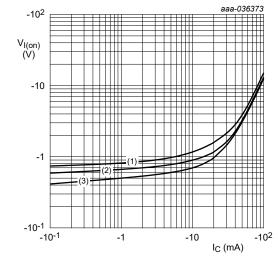
Fig. 11. TR2 (PNP): Collector current as a function of collector-emitter voltage; typical values



$$V_{CE} = -5 V$$

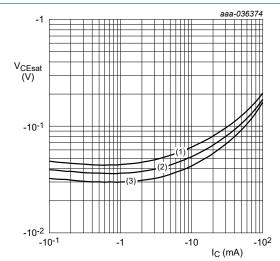
(1) $T_{amb} = -40 ^{\circ}C$
(2) $T_{amb} = 25 ^{\circ}C$
(3) $T_{amb} = 100 ^{\circ}C$

Fig. 12. TR2 (PNP): Off-state input voltage as a function of collector current; typical values



 $V_{CE} = -0.3 V$ (1) $T_{amb} = -40 \, ^{\circ}C$ (2) $T_{amb} = 25 \, ^{\circ}C$ (3) $T_{amb} = 100 \, ^{\circ}C$

of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$ (1) $T_{amb} = 100 \, ^{\circ}C$ $(2) T_{amb} = 25 °C$ (3) $T_{amb} = -40 \, ^{\circ}C$

Fig. 13. TR2 (PNP): On-state input voltage as a function | Fig. 14. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values

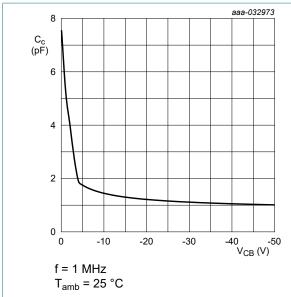


Fig. 15. TR2 (PNP): Collector capacitance as a function of collector-base voltage; typical values

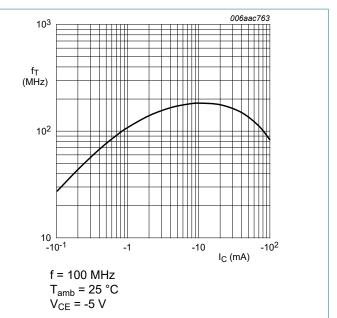


Fig. 16. TR2 (PNP): Transition frequency as a function of collector current; typical values of built-in transistor

11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

Resistor calculation

Calculation of bias resistor 1 (R1)

$$R_{I} = \frac{V(I_{2}) - V(I_{I})}{I_{2} - I_{I}}$$

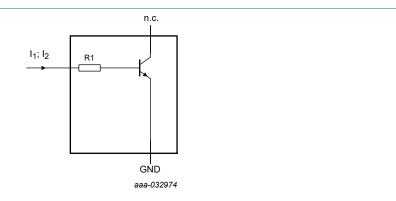


Fig. 17. TR1 (NPN): Resistor test circuit

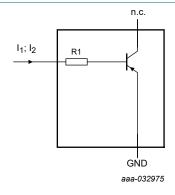


Fig. 18. TR2 (PNP): Resistor test circuit

Resistor test conditions

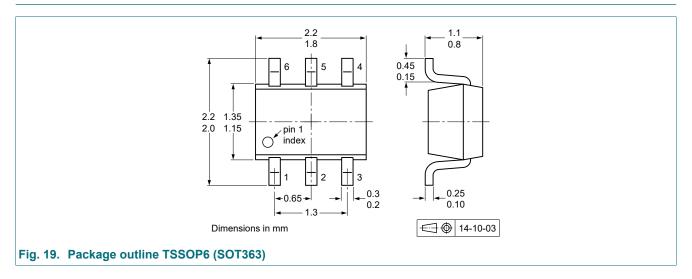
Table 8. Resistor test conditions

PUMD6	R1 (kΩ)	R2 (kΩ)	Test conditions	
			I ₁	l ₂
TR1 (NPN)	4.7	open	600 μΑ	700 μΑ
TR2 (PNP)	4.7	open	-600 μΑ	-700 μA

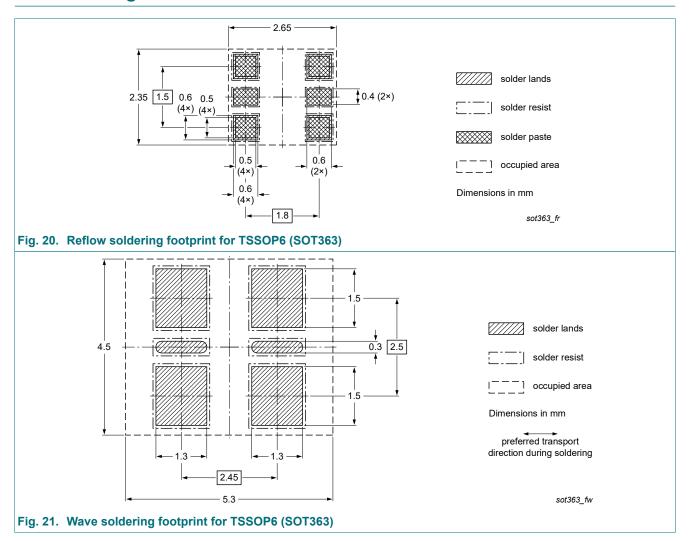
Nexperia PUMD6

50 V, 100 mA NPN/PNP Resistor-Equipped Transistor; R1 = 4.7 k Ω , R2 = open

12. Package outline



13. Soldering



14. Revision history

Table 9. Revision history

Table 9. Nevision history							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PUMD6 v.3	20230427	Product data sheet	-	PUMD6_PEMD6 v.2			
Modifications:	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. Family data sheet reduced to single type data sheet. 						
PUMD6_PEMD6 v.2	20040407	Product data sheet	-	PUMD6_PEMD6 v.1			
PUMD6_PEMD6 v.1	20031104	Product specification	-	-			

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50 V, 100 mA NPN/PNP Resistor-Equipped Transistor; R1 = 4.7 kΩ, R2 = open

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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